

1.2V Drive Nch + Nch MOSFET

EM6K33

●Structure

Silicon N-channel MOSFET

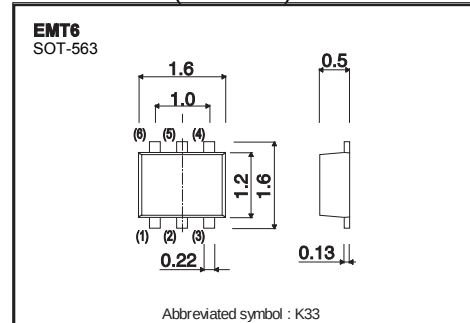
●Features

- 1) High speed switing.
- 2) Small package(EMT6).
- 3) Ultra low voltage drive(1.2V drive).

●Application

Switching

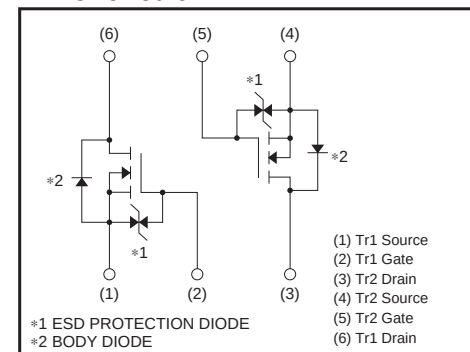
●Dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	T2R
	Basic ordering unit (pieces)	8000
EM6K33		○

●Inner circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	50	V
Gate-source voltage		V _{GSS}	±8	V
Drain current	Continuous	I _D	±200	mA
	Pulsed	I _{DP} *1	±800	mA
Source current (Body Diode)	Continuous	I _s	125	mA
	Pulsed	I _{sp} *1	800	mA
Power dissipation		P _D *2	150	mW / TOTAL
			120	mW / ELEMENT
Channel temperature		T _{ch}	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

 *1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 Each terminal mounted on a recommended land.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th}(ch-a)^*$	833	°C / W / TOTAL
		1042	°C / W / ELEMENT

* Each terminal mounted on a recommended land.

●Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 50V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	1.0	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	Ω	$I_D = 200mA, V_{GS} = 4.5V$
		-	1.7	2.4		$I_D = 200mA, V_{GS} = 2.5V$
		-	1.9	2.7		$I_D = 100mA, V_{GS} = 1.8V$
		-	2.0	4.0		$I_D = 40mA, V_{GS} = 1.5V$
		-	2.4	7.2		$I_D = 20mA, V_{GS} = 1.2V$
Forward transfer admittance	$ Y_{fs} ^*$	0.4	-	-	S	$I_D = 200mA, V_{DS} = 10V$
Input capacitance	C_{iss}	-	25	-	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	-	6	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	3	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	4	-	ns	$I_D = 100mA, V_{DD} = 30V$
Rise time	t_r^*	-	6	-	ns	$V_{GS} = 4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	15	-	ns	$R_L = 300\Omega$
Fall time	t_f^*	-	55	-	ns	$R_G = 10\Omega$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}^*	-	-	1.2	V	$I_S = 200mA, V_{GS} = 0V$

*Pulsed

●Electrical characteristic curves

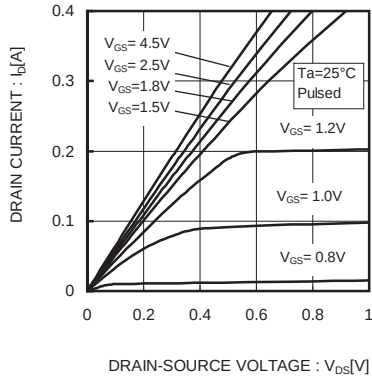


Fig.1 Typical Output Characteristics(I)

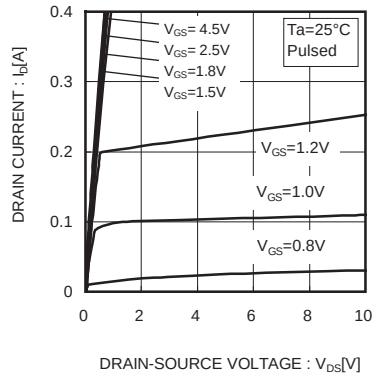


Fig.2 Typical Output Characteristics(II)

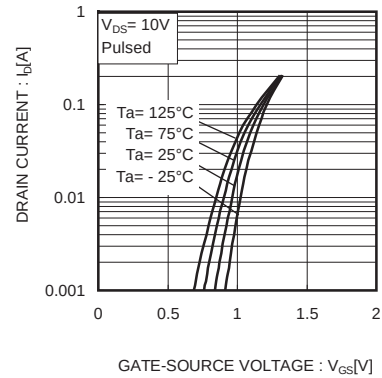


Fig.3 Typical Transfer Characteristics

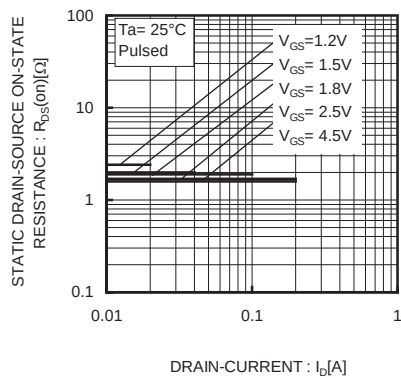


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

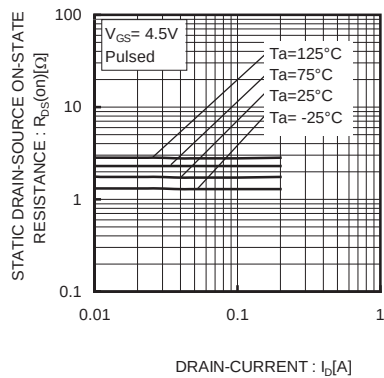


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

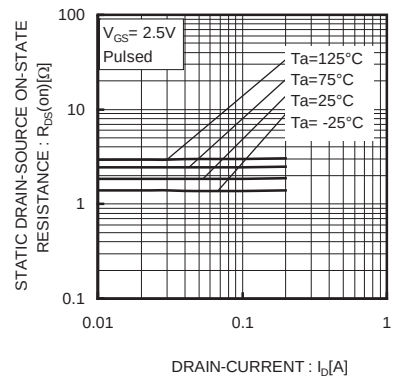


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

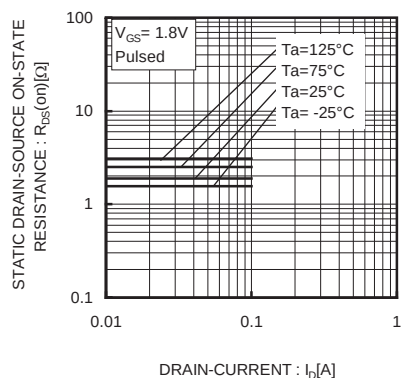


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

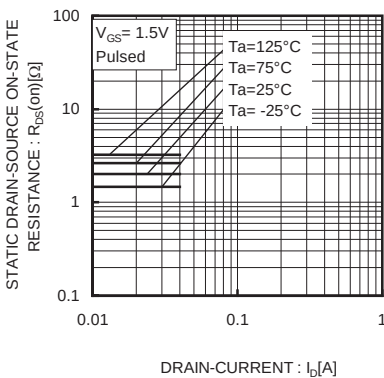


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

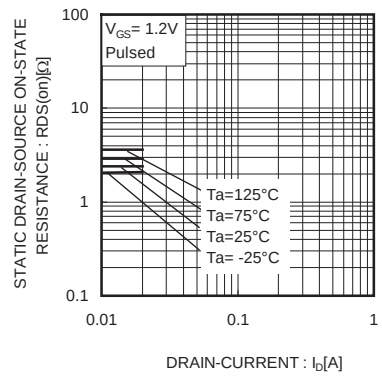


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI)

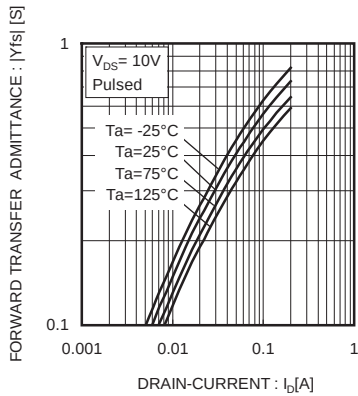


Fig.10 Forward Transfer Admittance vs. Drain Current

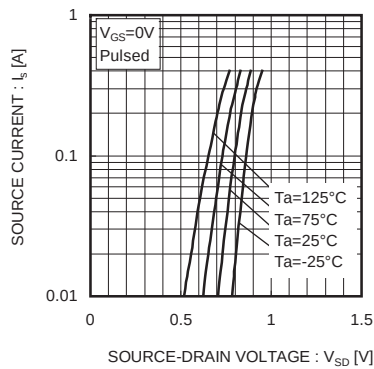


Fig.11 Reverse Drain Current vs. Source-Drain Voltage

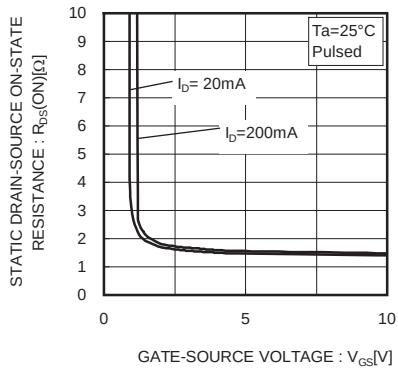


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

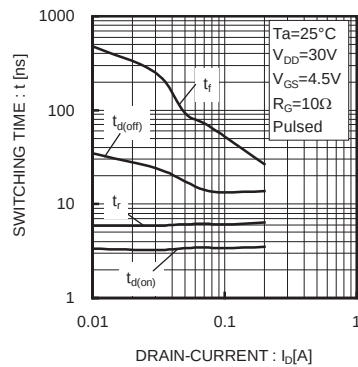


Fig.13 Switching Characteristics

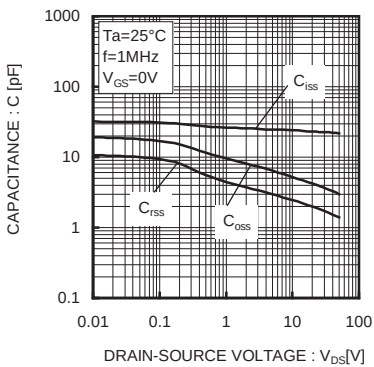


Fig.14 Typical Capacitance vs. Drain-Source Voltage

●Measurement circuits

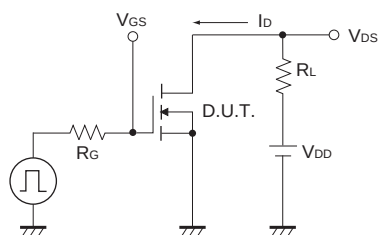


Fig.1-1 Switching time measurement circuit

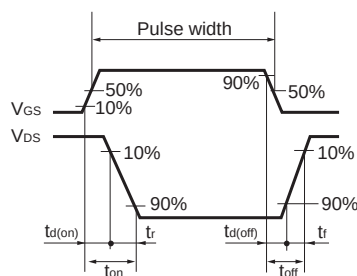


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

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